**Product data sheet** 

# 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in an MLPAK33 (SOT8002) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Logic-level compatible
- Trench MOSFET technology
- Ultra low Q<sub>G</sub> and Q<sub>GD</sub> for high system efficiency, especially at higher switching frequencies
- Superfast switching with soft-recovery
- · Low spiking and ringing for low EMI designs
- MLPAK33 package (3.3 x 3.3 mm footprint)

### 3. Applications

- DC to DC conversion
- · Battery management
- · Low-side load switch
- · Switching circuits

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	25	V
$V_{GS}$	gate-source voltage			-20	-	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	-	19	А
Static charac	teristics						
R <sub>DSon</sub> drain-source on-s	drain-source on-state	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 11.8 A; T <sub>j</sub> = 25 °C		-	6.6	7.7	mΩ
	resistance	$V_{GS} = 4.5 \text{ V}; I_D = 9.8 \text{ A}; T_j = 25 ^{\circ}\text{C}$		-	8.9	11.1	mΩ
Dynamic cha	racteristics					·	
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = 12.5 V; $I_{D}$ = 9.8 A; $V_{GS}$ = 4.5 V; $T_{j}$ = 25 °C		-	5.3	8	nC

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



25 V, N-channel Trench MOSFET

# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	1 2 3 4	D
2	S	source		
3	S	source		G—(FA)
4	G	gate	ि त	mbb076 S
5	D	drain		
6	D	drain		
7	D	drain	MLPAK33 (SOT8002-1)	
8	D	drain		

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package							
	Name	Description	Version					
PXN7R7-25QL		plastic thermal enhanced surface mounted package; mini leads; 8 terminals; pitch 0.65 mm; 3.3 x 3.3 x 0.8 mm body	SOT8002-1					

# 7. Marking

#### Table 4. Marking codes

Type number	Marking code
PXN7R7-25QL	9AE

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# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	25	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	19	Α
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	11.8	Α
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C	[1]	-	7.5	Α
		V <sub>GS</sub> = 10 V; T <sub>sp</sub> = 25 °C		-	32	Α
I <sub>DM</sub>	peak drain current	T <sub>amb</sub> = 25 °C; single pulse; t <sub>p</sub> ≤ 10 μs		-	102	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	4.3	W
		T <sub>amb</sub> = 25 °C	[1]	-	1.7	W
		T <sub>sp</sub> = 25 °C		-	12.5	W
T <sub>j</sub>	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drain o	diode		'	<u> </u>		
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	1.5	Α
Avalanche rug	gedness		'	'		
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	T <sub>j(init)</sub> = 25 °C; I <sub>D</sub> = 1.8 A; DUT in avalanche (unclamped)		-	22.5	mJ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.

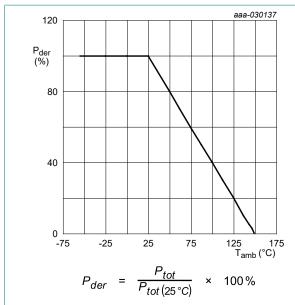


Fig. 1. Normalized total power dissipation as a function of ambient temperature

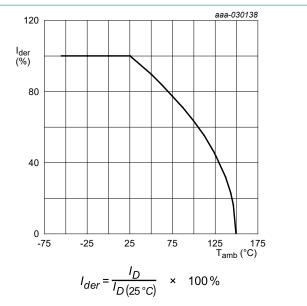


Fig. 2. Normalized continous drain current as a function of ambient temperature

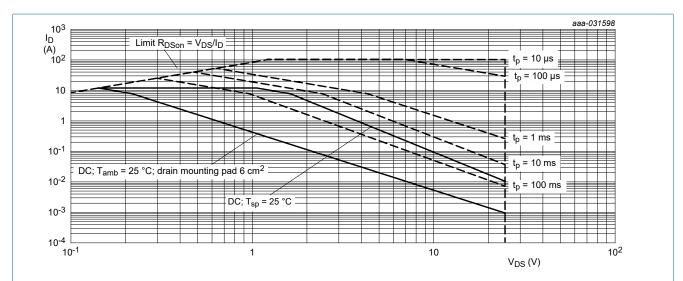


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

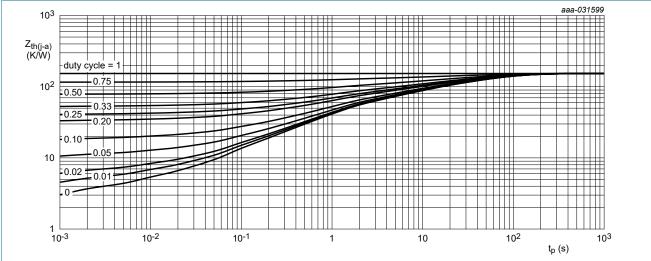
25 V, N-channel Trench MOSFET

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

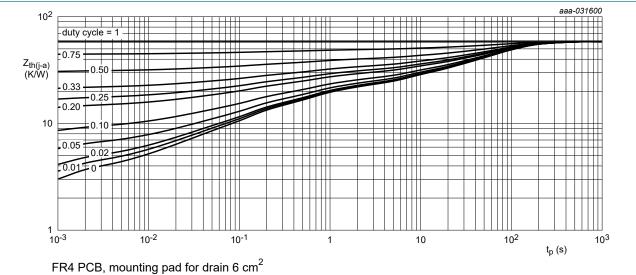
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from	in free air	[1]	-	150	190	K/W
	junction to ambient		[2]	-	60	75	K/W
		in free air; t ≤ 5 s	[2]	-	24	29	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	7	10	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



FR4 PCB, standard footprint

Transient thermal impedance from junction to ambient as a function of pulse duration; typical values Fig. 4.



Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

25 V, N-channel Trench MOSFET

# 10. Characteristics

#### Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		l l			
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	25	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1.2	1.7	2.2	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 25 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	0.1	μA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-0.1	μΑ
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 11.8 A; T <sub>j</sub> = 25 °C	-	6.6	7.7	mΩ
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 11.8 A; T <sub>j</sub> = 150 °C	-	10.2	11.9	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 9.8 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	8.9	11.1	mΩ
9fs	forward transconductance	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 11.8 A; T <sub>j</sub> = 25 °C	-	25	-	S
R <sub>G</sub>	gate resistance	f = 1 MHz	-	2.3	-	Ω
Dynamic ch	naracteristics		<u> </u>	'		
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = 12.5 V; $I_{D}$ = 11.8 A; $V_{GS}$ = 10 V; $I_{j}$ = 25 °C	-	11.1	16.6	nC
		$V_{DS}$ = 12.5 V; $I_D$ = 9.8 A; $V_{GS}$ = 4.5 V;	-	5.3	8	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	2	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate- source charge		-	1.2	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate- source charge		-	0.8	-	nC
Q <sub>GD</sub>	gate-drain charge		-	1.5	-	nC
$V_{GSpl}$	gate-source plateau voltage	$V_{DS}$ = 12.5 V; $I_D$ = 9.8 A; $T_j$ = 25 °C	-	2.8	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 12.5 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	770	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	310	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	55	-	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 12.5 V; I <sub>D</sub> = 9.8 A; V <sub>GS</sub> = 4.5 V;	-	5	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 °C$	-	8	-	ns
$t_{d(off)}$	turn-off delay time		-	6	-	ns
t <sub>f</sub>	fall time		-	3	-	ns
Source-dra	in diode		<u> </u>			
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 1.5 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.7	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 1.5 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	15	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = 4.5 \text{ V}; V_{DS} = 12.5 \text{ V}; T_j = 25 \text{ °C}$	-	6	-	nC
t <sub>a</sub>	reverse recovery rise time		-	8	-	ns
t <sub>b</sub>	reverse recovery fall time	1	-	7	-	ns

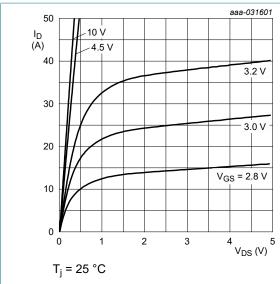


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

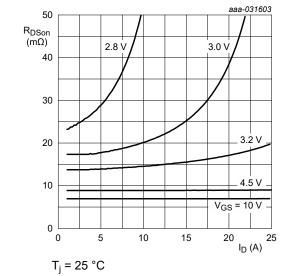


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

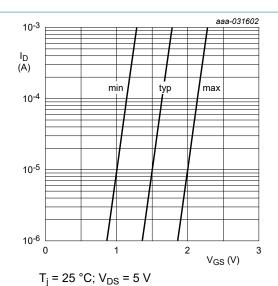


Fig. 7. Subthreshold drain current as a function of gate-source voltage

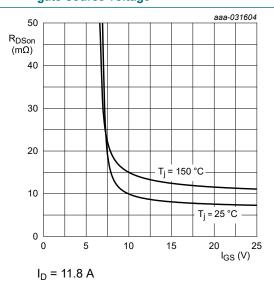


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

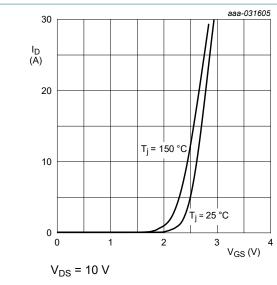


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

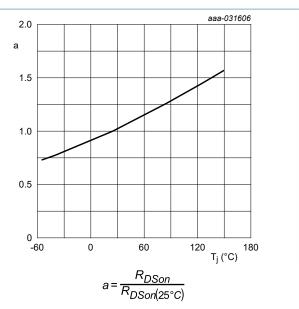


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

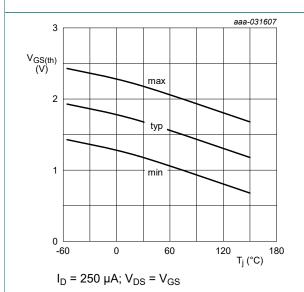
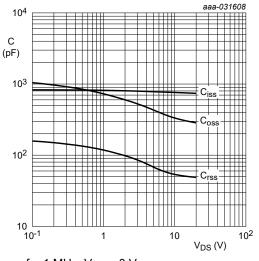


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$ 

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

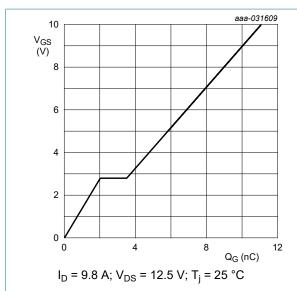


Fig. 14. Gate-source voltage as a function of gate charge; typical values

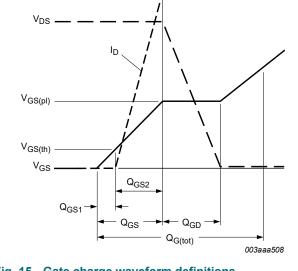


Fig. 15. Gate charge waveform definitions

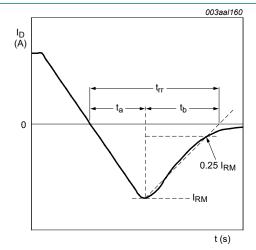


Fig. 16. Reverse recovery timing definition

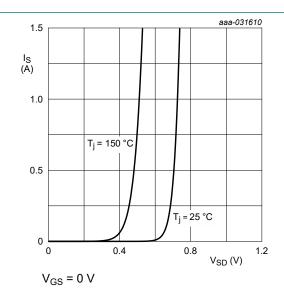
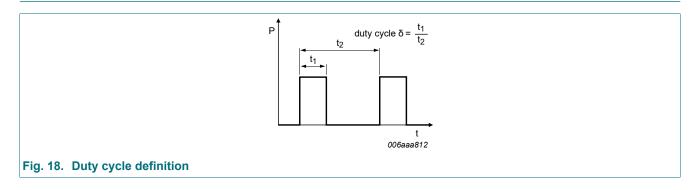


Fig. 17. Source current as a function of source-drain voltage; typical values

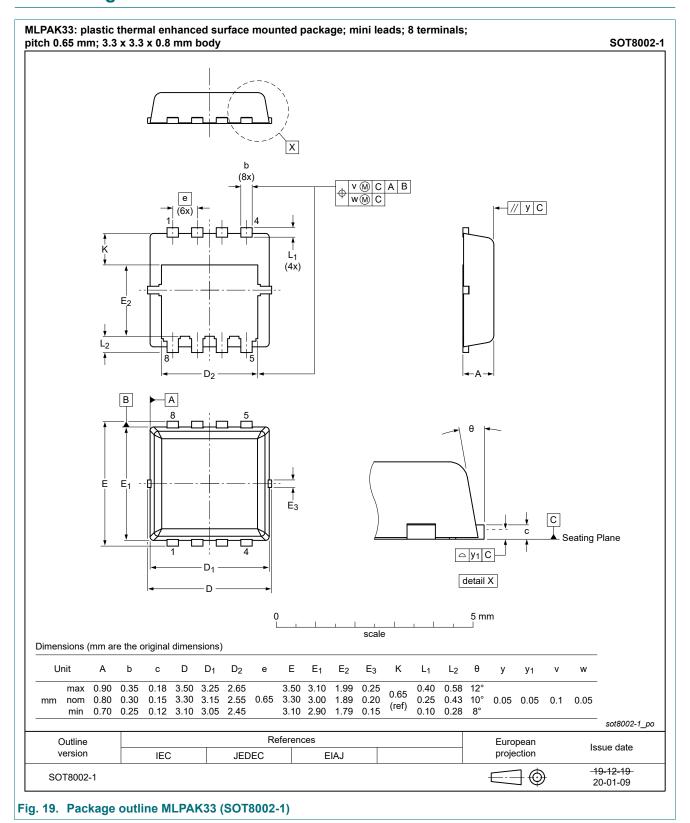
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# 11. Test information



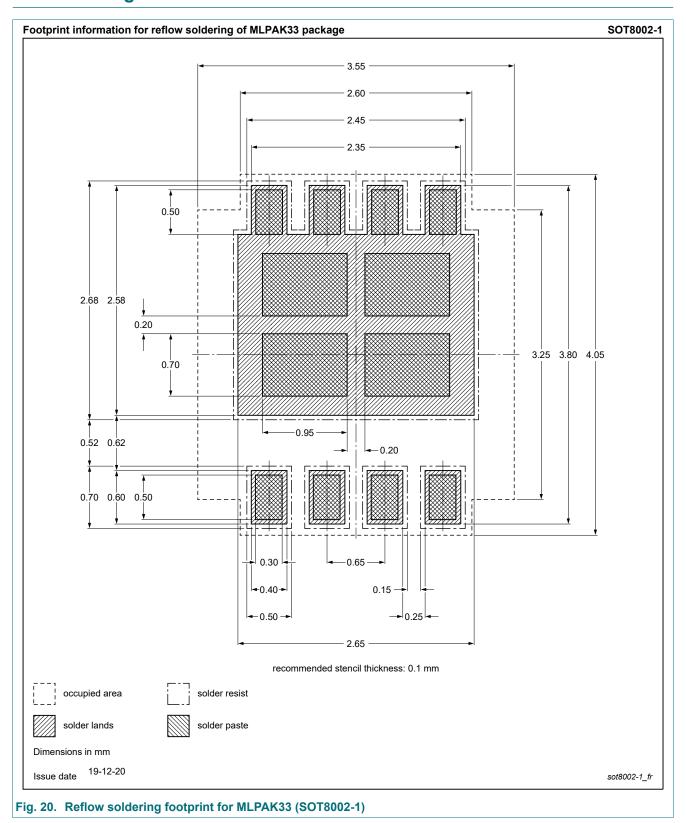
25 V, N-channel Trench MOSFET

# 12. Package outline



25 V, N-channel Trench MOSFET

# 13. Soldering



25 V, N-channel Trench MOSFET

# 14. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PXN7R7-25QL v.1	20201102	Product data sheet	-	-

#### 25 V, N-channel Trench MOSFET

### 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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